NEC

MOS FIELD EFFECT TRANSISTOR
2SK3116

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

Description

The 2SK3116 is N channel DMOS FET device that features a low gate charge and excellent switching characteristics, and designed for high voltage applications such as switching power supply, AC adapter.

Ordering Information

Part number	Package
2SK3116	TO-220
2SK3116-S	TO-262
2SK3116-ZJ	TO-263

Features

- Low gate charge
  Q_G = 26 nC TYP. (V_{DD} = 450 V, V_{GS} = 10 V, I_D = 7.5 A)
- Gate voltage rating ±30 V
- Low on-state resistance
  $R_{DS(on)}$ = 1.2 Ω (MAX.) (V_{GS} = 10 V, I_D = 3.75 A)
- Avalanche capability ratings

Absolute Maximum Rating (T_A = 25°C)

Drain to source voltage (V_{GS} = 0 V)	V_{DSS}	600	V
Gate to source voltage (V_{DS} = 0 V)	V_{GSS}	±30	V
Drain current (DC) (T_C = 25°C)	$I_{D(DC)}$	±7.5	A
Drain current (pulse) Note1	$I_{D(pulse)}$	±30	A
Total power dissipation (T_A = 25°C)	P_{T1}	1.5	W
Total power dissipation (T_C = 25°C)	P_{T2}	70	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C
Single avalanche current Note2	I_{AS}	7.5	A
Single avalanche energy Note2	E_{AS}	37.5	mJ
Diode recovery dv/dt Note3	dt/dt	3.5	V/ns

Notes 1. PW ≤ 10 μs, Duty cycle ≤ 1 %

2. Starting T_{ch} = 25°C, V_{DD} = 150 V, R_G = 25 Ω , V_{GS} = 20 V→0 V

3. I_F ≤ 3.0 A, V_{clamp} = 600 V, di/dt ≤ 100 A/μs, T_A = 25°C

The information in this document is subject to change without notice.

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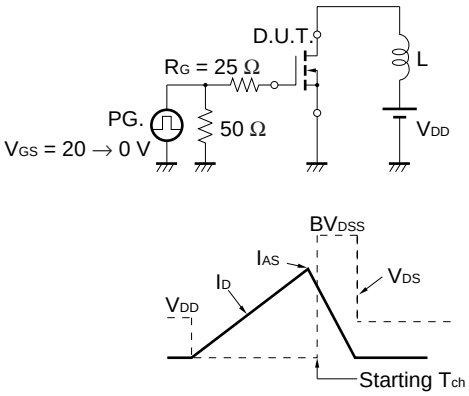
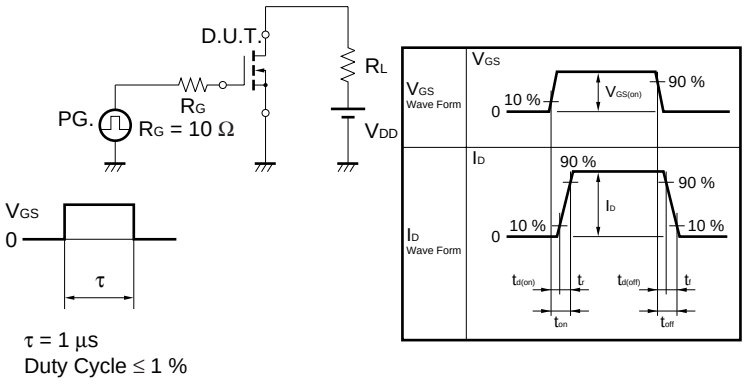
Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Drain leakage current	I_{DSS}			100	μA	V_{DS} = 600 V, V_{GS} = 0 V
Gate leakage current	I_{GSS}			±100	nA	V_{GS} = ±30 V, V_{DS} = 0 V
Gate cut-off voltage	$V_{GS(off)}$	2.5		3.5	V	V_{DS} = 10 V, I_D = 1 mA
Forward transfer admittance	$\|y_{fs}\|$	2.0			S	V_{DS} = 10 V, I_D = 3.75 A
Drain to source on-state resistance	$R_{DS(on)}$		0.9	1.2	Ω	V_{GS} = 10 V, I_D = 3.75 A
Input capacitance	C_{iss}		1100		pF	V_{DS} = 10 V
Output capacitance	C_{oss}		200		pF	V_{GS} = 0 V
Reverse transfer capacitance	C_{rss}		20		pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$		18		ns	V_{DD} = 150 V, I_D = 3.75 A
Rise time	t_r		15		ns	$V_{GS(on)}$ = 10 V
Turn-off delay time	$t_{d(off)}$		50		ns	R_G = 10 Ω
Fall time	t_f		15		ns	R_L = 50 Ω
Total gate charge	Q_G		26		nC	V_{DD} = 450 V
Gate to source charge	Q_{GS}		6		nC	V_{GS} = 10 V
Gate to drain charge	Q_{GD}		10		nC	I_D = 7.5 A
Diode forward voltage	$V_{F(S-D)}$		1.0		V	I_F = 7.5 A, V_{GS} = 0 V
Reverse recovery time	T_{rr}		1.6		μs	I_F = 7.5 A, V_{GS} = 0 V
Reverse recovery charge	Q_{rr}		7.6		μC	di/dt = 50 A/μs

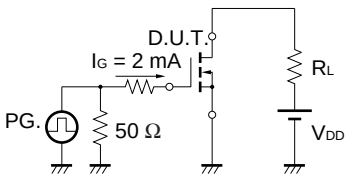
Test circuit 1 Avalanche capability



Test circuit 2 Switching time

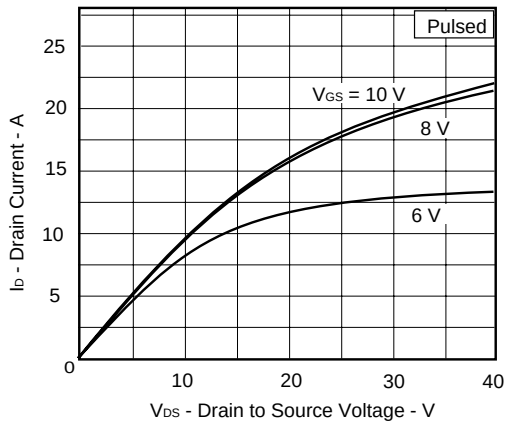


Test circuit 3 Gate charge

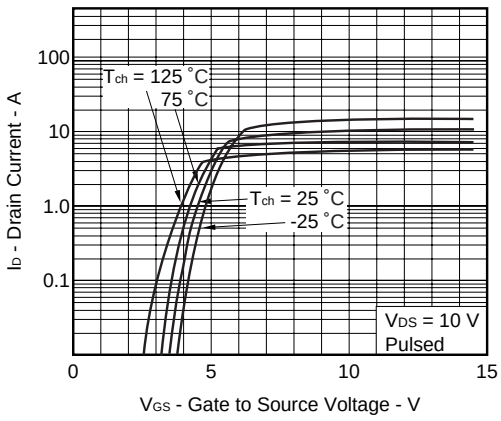


Typical Characteristics(T_A = 25°C)

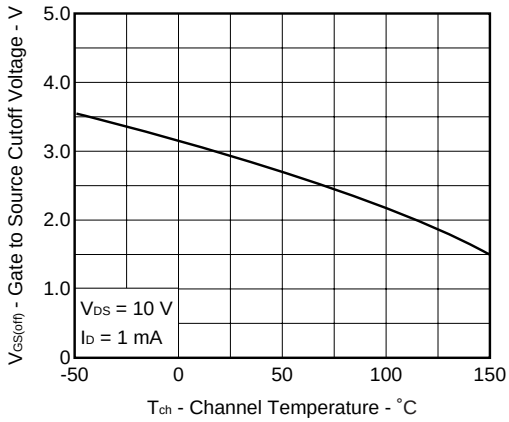
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



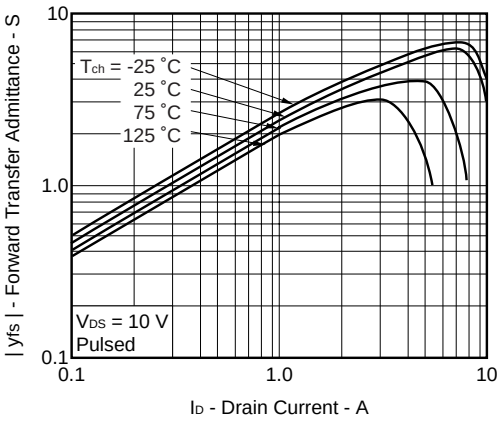
FORWARD TRANSFER CHARACTERISTICS



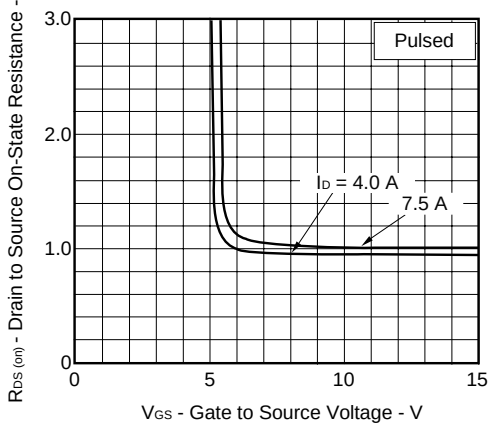
GATE TO SOURCE CUTOFF VOLTAGE
vs. CHANNEL TEMPERATURE



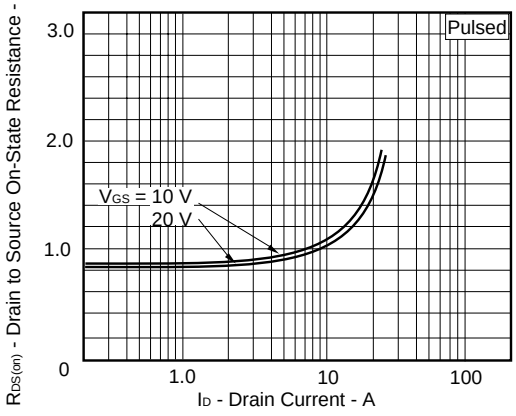
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



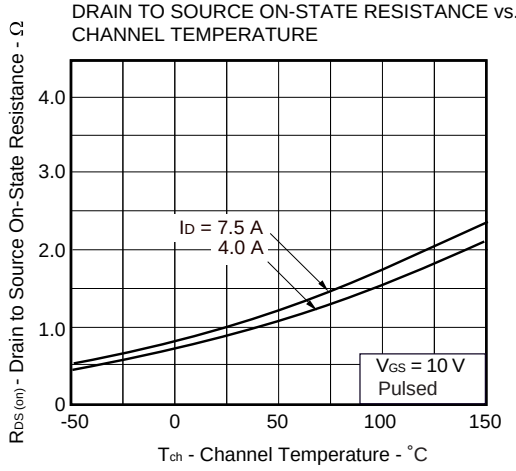
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



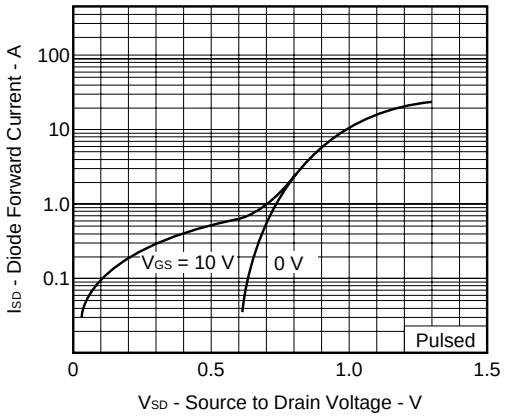
DRAIN TO SOURCE ON-STATE
RESISTANCE vs. DRAIN CURRENT



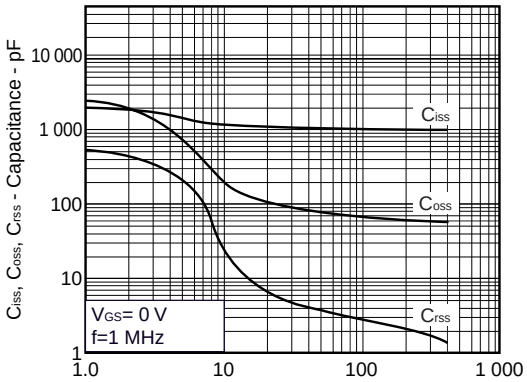
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



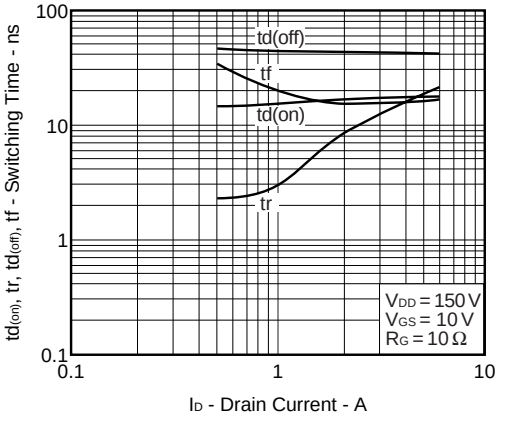
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



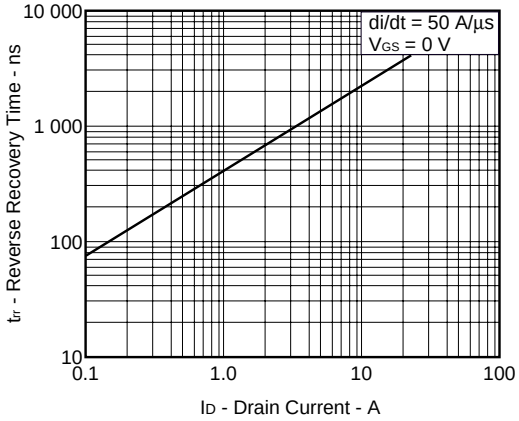
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



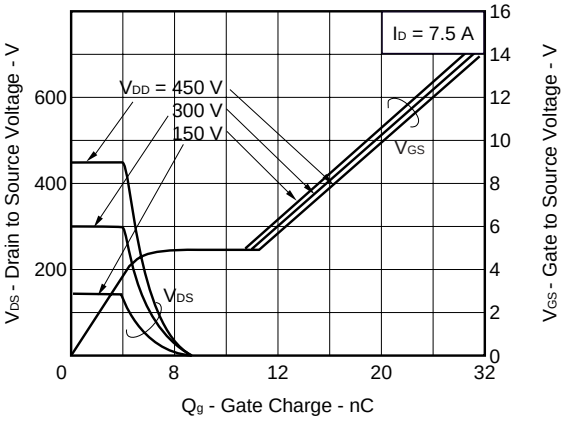
SWITCHING CHARACTERISTICS



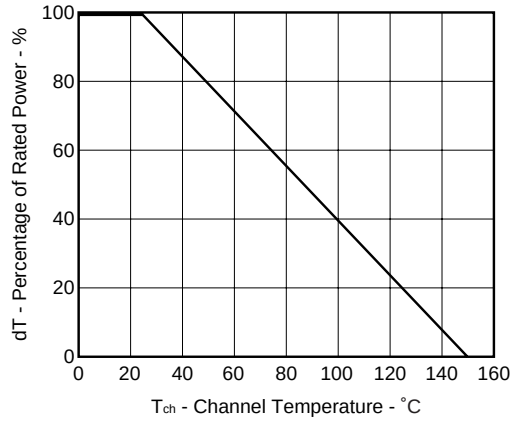
REVERSE RECOVERY TIME vs. DRAIN CURRENT



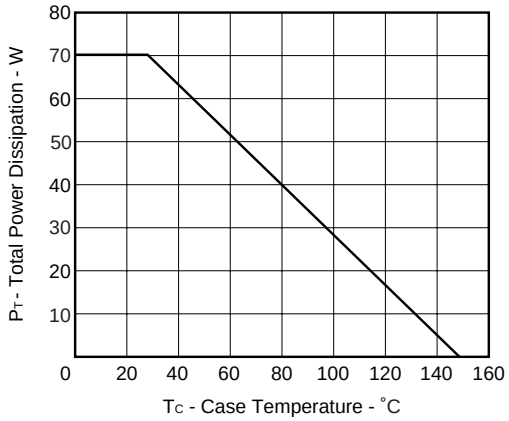
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



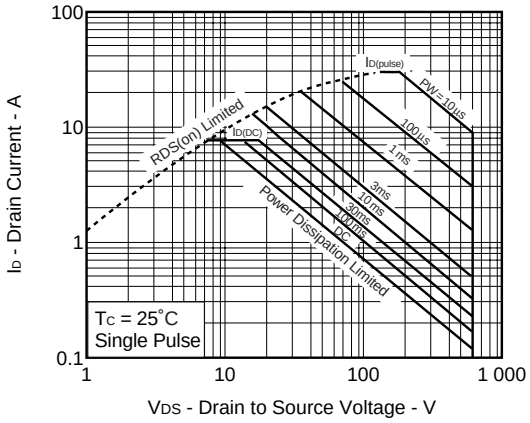
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



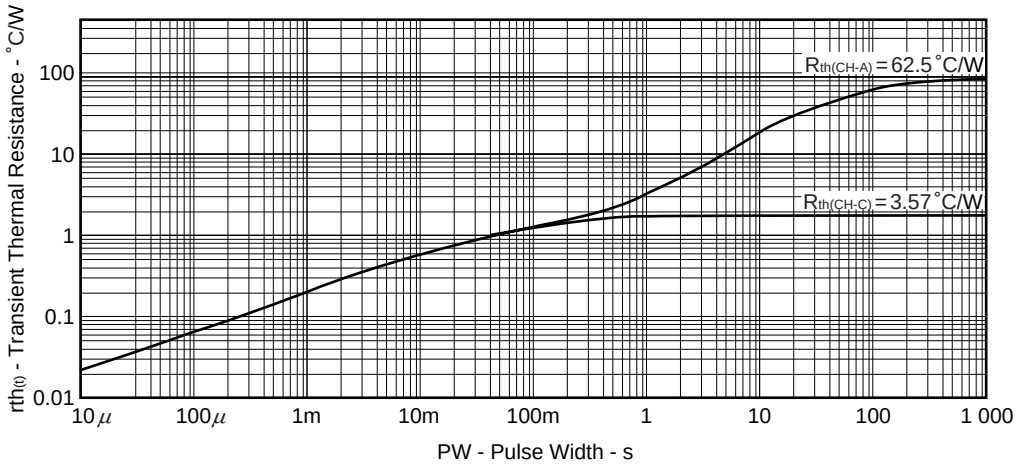
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



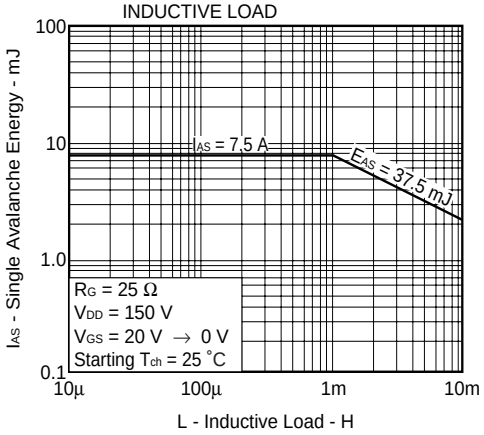
FORWARD BIAS SAFE OPERATING AREA



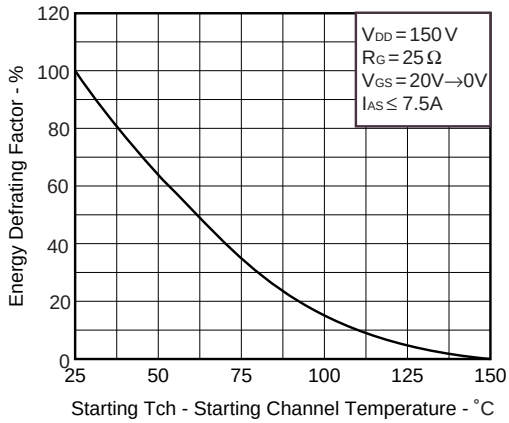
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



SINGLE AVALANCHE ENERGY vs.
INDUCTIVE LOAD

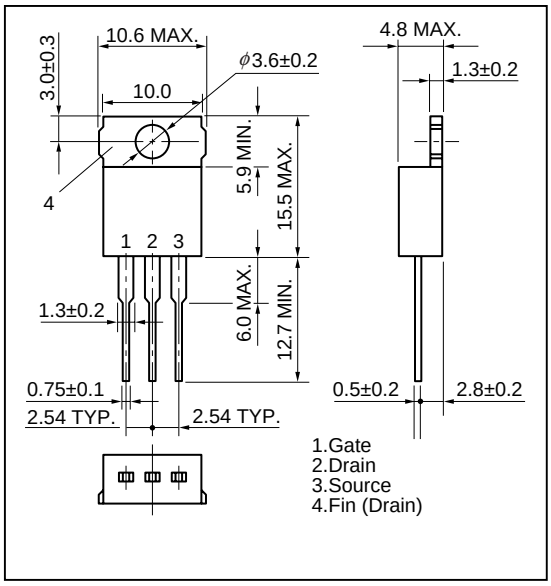


SINGLE AVALANCHE ENERGY
DERATING FACTOR

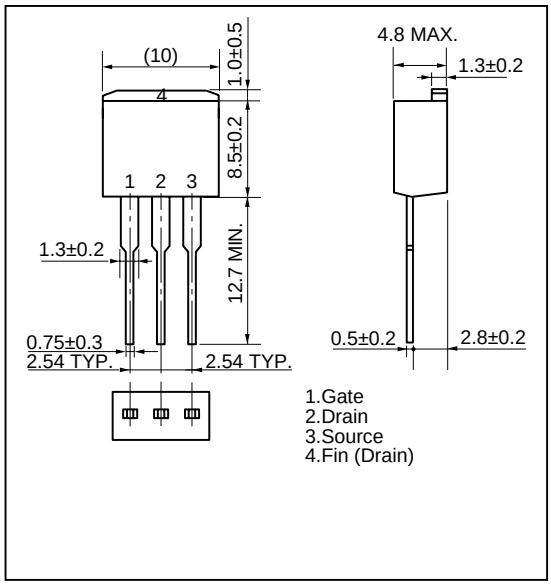


Package Drawing (Unit : mm)

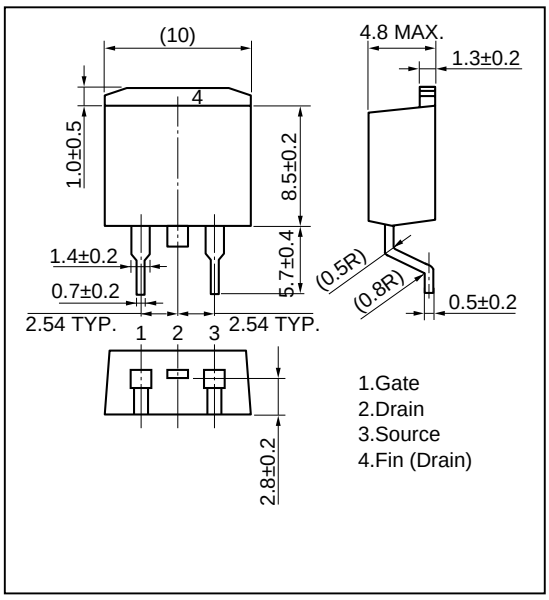
1)TO-220AB (MP-25)



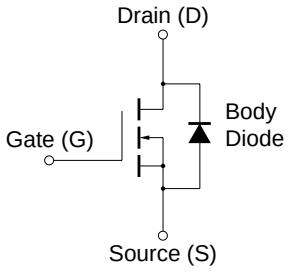
2)TO-262 (TO-220 Fin Cut:MP-25S)



3)TO-263 (JEDEC TYPE:MP-25ZJ)



Equivalent Circuit



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.